

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device having at least one thin film transistor, said thin film transistor comprising:

a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and

a gate electrode formed adjacent to said semiconductor layer,

wherein said semiconductor layer comprises crystals ~~arranged in a direction substantially~~  
in which crystal grain boundaries are substantially aligned in a direction parallel with a length direction of said channel formation region,

wherein a standard deviation of S-value of said thin film transistor is within 10 mV/dec for an N-channel type and 15 mV/dec for a P-channel type.

2. (Original) A semiconductor device according to claim 1, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

3. (Original) A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.

4. (Currently Amended) A semiconductor device having at least one thin film transistor, said thin film transistor comprising:

a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and  
a gate electrode formed adjacent to said semiconductor layer,  
wherein said semiconductor layer comprises crystals ~~arranged in a direction~~  
substantially in which crystal grain boundaries are aligned in a direction parallel with a length  
direction of said channel formation region,  
wherein a length of said channel formation region is 0.01 to 2  $\mu\text{m}$ .

5. (Original) A semiconductor device according to claim 4, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

6. (Original) A semiconductor device according to claim 4, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.

7. (Currently Amended) A semiconductor device having at least one thin film transistor, said thin film transistor comprising:

a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and  
a gate electrode formed adjacent to said semiconductor layer,  
wherein said semiconductor layer comprises crystals ~~arranged in a direction~~  
substantially in which crystal grain boundaries are aligned in a direction parallel with a carrier  
flow direction between said source and drain regions,  
wherein a standard deviation of S-value of said thin film transistor is within 10 mV/dec for an N-channel type and 15 mV/dec for a P-channel type.

8. (Original) A semiconductor device according to claim 7, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

9. (Original) A semiconductor device according to claim 7, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.

10. (Currently Amended) A semiconductor device having at least one thin film transistor, said thin film transistor comprising:  
a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and  
a gate electrode formed adjacent to said semiconductor layer,  
wherein said semiconductor layer comprises crystals ~~arranged in a direction~~  
substantially in which crystal grain boundaries are aligned in a direction parallel with a carrier flow direction between said source and drain regions,  
wherein a length of said channel formation region is 0.01 to 2  $\mu\text{m}$ .

11. (Original) A semiconductor device according to claim 10, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

12. (Original) A semiconductor device according to claim 10, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.

13. (Currently Amended) An active matrix display device comprising:  
a pixel matrix circuit formed over a substrate;  
a logic circuit formed over said substrate, said logic circuit having thin film transistors,  
wherein each of said thin film transistors comprises:  
a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and  
a gate electrode formed adjacent to said semiconductor layer,  
wherein said semiconductor layer comprises crystals ~~arranged in a direction~~ substantially in which crystal grain boundaries are aligned in a direction parallel with a length direction of said channel formation region,  
wherein a standard deviation of S-value of said thin film transistor is within 10 mV/dec for an N-channel type and 15 mV/dec for a P-channel type.

14. (Original) An active matrix display device according to claim 13, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

15. (Original) An active matrix display device according to claim 13, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.

16. (Currently Amended) An active matrix display device comprising:  
a pixel matrix circuit formed over a substrate;  
a logic circuit formed over said substrate, said logic circuit having thin film transistors,  
wherein each of said thin film transistors comprises:

a semiconductor layer formed over a substrate, said semiconductor layer having source and drain regions and a channel formation region interposed therebetween; and  
a gate electrode formed adjacent to said semiconductor layer,  
wherein said semiconductor layer comprises crystals ~~arranged in a direction~~  
substantially in which crystal grain boundaries are aligned in a direction parallel with a carrier flow direction between said source and drain regions,  
wherein a standard deviation of S-value of said thin film transistor is within 10 mV/dec for an N-channel type and 15 mV/dec for a P-channel type.

17. (Original) An active matrix display device according to claim 16, wherein said semiconductor layer contains a metal element for promoting crystallization at a concentration of not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.

18. (Original) An active matrix display device according to claim 16, wherein said semiconductor device is incorporated into an electronic apparatus selected from the group consisting of a TV camera, a head mounted display, a car navigation, a portable telephone, a video camera and a projector.